Title (en)

METHOD FOR FABRICATING LOW-RESISTANCE CONTACTS ON NITRIDE SEMICONDUCTOR DEVICES

Title (de)

VERFAHREN ZUM HERSTELLEN VON KONTAKTEN MIT NIEDRIGEM WIDERSTAND AUF HALBLEITERANORDNUNGEN AUS EINER NITRIDVERBINDUNG

Title (fr)

PROCEDE DE FABRICATION DE CONTACTS A FAIBLE RESISTANCE SUR DES DISPOSITIFS A SEMI-CONDUCTEURS DE NITRURE

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EP 0972310 A1 20000119 (EN)

Application

EP 98906549 A 19980218

Priority

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- US 9803146 W 19980218

Abstract (en)

[origin: WO9837586A1] A method for fabricating an electrical contact (12) on a surface (11) of a semiconductor comprising a group III element and nitrogen. The contact (12) is formed by depositing a metallic layer on the semiconductor surface and then annealing the layer at a tempeature greater than 400 DEG C for at least 4 hours. The method can be used to construct a Au/Ni contact on GaN semiconductor surface with substantially less resistivity than that obtained by conventional methods.

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